

/ Descriptions

TO-252 PNP Silicon PNP transistor in a TO-252 Plastic Package.

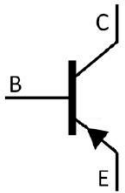
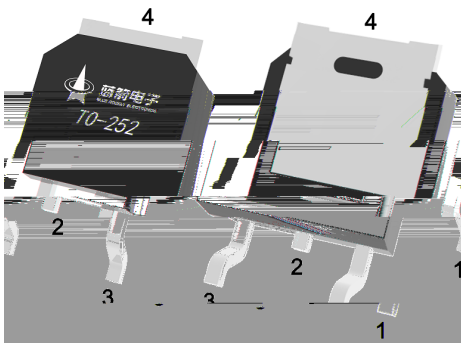
/ Features

AEC-Q101

Low Speed ,Load Formed for Surface Mount Application, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

/ Applications

General Purpose Amplifier, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit**/ Pinning**

PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

BRMJD32CQ

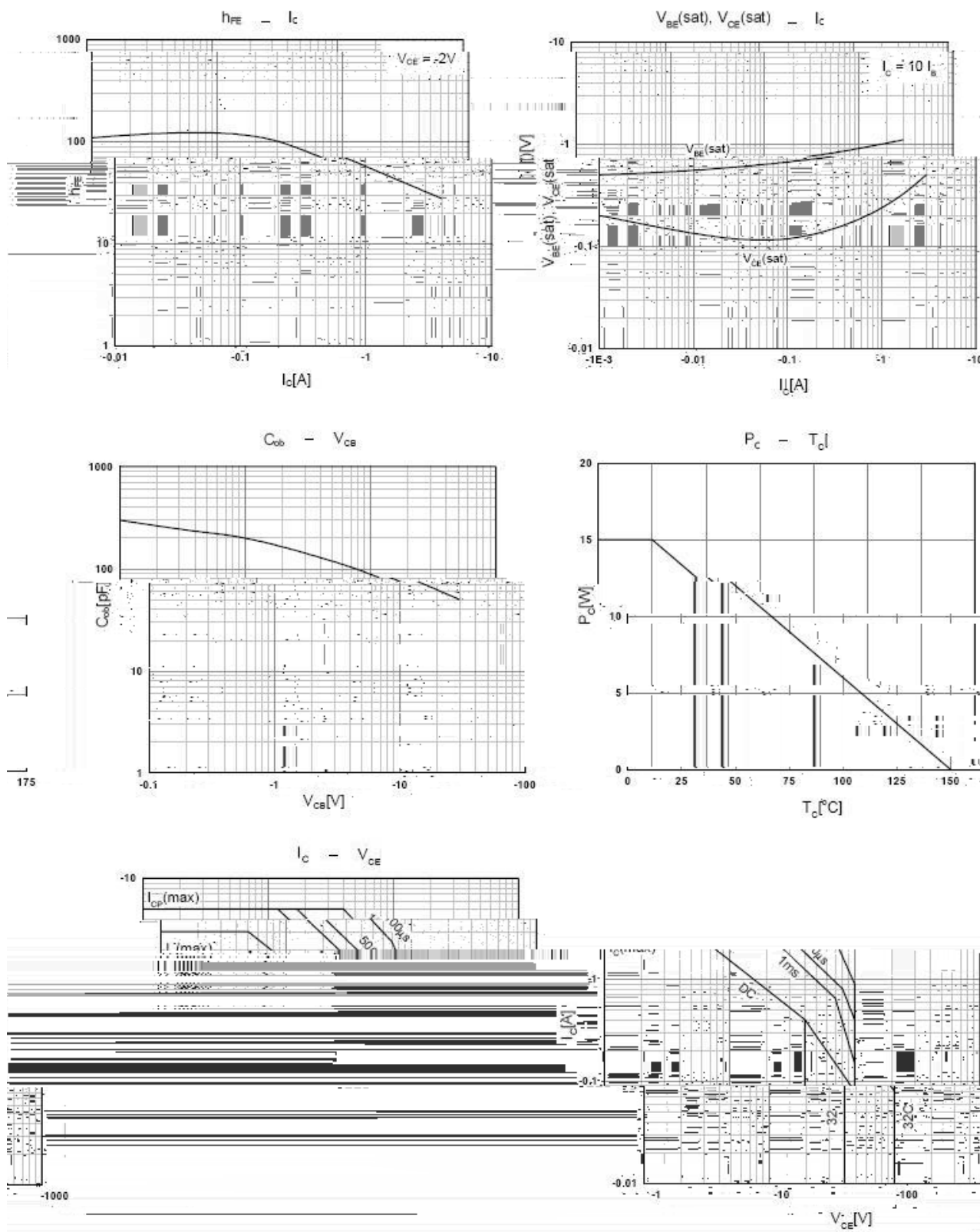
Rev.A Apr.-2024



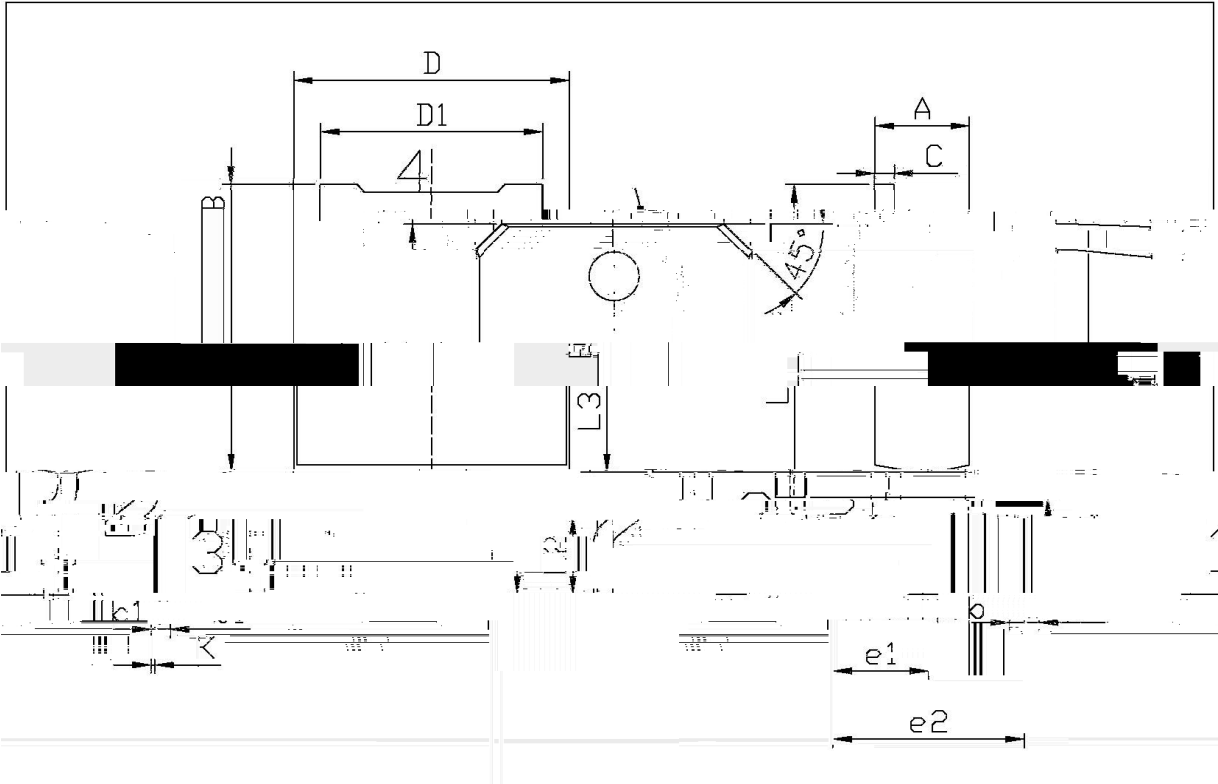
DATA SHEET

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V

/ Electrical Characteristic Curve



/ Package Dimensions

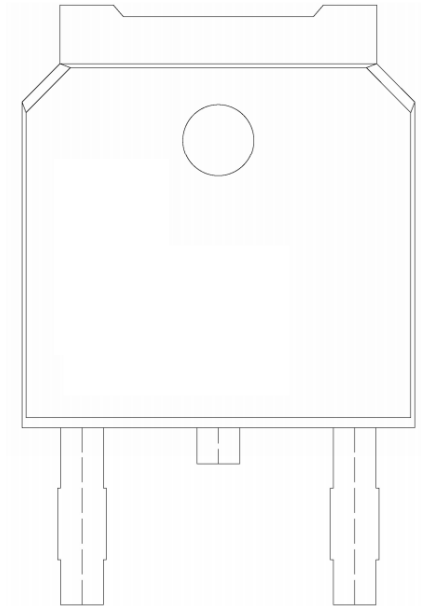


单位: mm

Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
E	5.95	6.25	A	2.20	2.40
e1	2.24	2.34	R	0.95	1.25
0.45	0.55	L1	9.85	10.35	b1
0.60	0.90	0.55	1.2	1.70	2.00
0.60	0.90	0.55	6.45	6.75	L3
0.60	0.90	0.55	D1	5.40	5.50

32 TO=21

/ Marking Instructions



BR
Q
MJD32C

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1

150 200

60 120sec;

1.Preheating:150~200 , Time:60~120sec.
- 2

255±5

5±0.5sec;

2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 /sec.